

DESCRIPTION:

With high ability to withstand the shock loading of large current, BTB20-800CW series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.



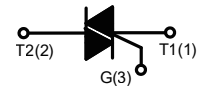
TO-3P



TO-220F



TO-220A


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	20	A
V_{DRM}/V_{RRM}	600/800/1200	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	600/800/1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	600/800/1200	V
Non repetitive surge peak Off-state voltage		V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-220A(Ins) ($T_C=70^\circ\text{C}$)	$I_{T(RMS)}$	20	A
	TO-220A(Non-Ins) ($T_C=90^\circ\text{C}$)			
	TO-220F(Ins) ($T_C=65^\circ\text{C}$)			
	TO-3P(Ins) ($T_C=105^\circ\text{C}$)			

Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	200	A
I^2t value for fusing ($t_p=10ms$)	I^2t	200	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	100	$A/\mu s$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

3 Quadrants

Symbol	Test Condition	Quadrant		Value		Unit
				BW	CW	
I_{GT}	$V_D=12V R_L=33\Omega$	I - II -III	MAX	50	35	mA
V_{GT}		I - II -III	MAX	1.3		V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C$ $R_L=3.3K\Omega$	I - II -III	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	70	60	mA
		II		90	70	
I_H	$I_T=100mA$		MAX	60	50	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ C$		MIN	1000	500	$V/\mu s$

4 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12V R_L=33\Omega$	I - II -III	MAX	50	mA
		IV		70	
V_{GT}		ALL	MAX	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C$ $R_L=3.3K\Omega$	ALL	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III-IV	MAX	70	mA
		II		90	
I_H	$I_T=100mA$		MAX	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ C$		MIN	500	$V/\mu s$

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM} = 28A$ $t_p = 380\mu s$	$T_j = 25^\circ C$	1.5	V
I_{DRM}	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_j = 25^\circ C$	5	μA
I_{RRM}		$T_j = 125^\circ C$	2.5	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	1.9	$^\circ C/W$
		TO-220A(Non-Ins)	1.1	
		TO-220F(Ins)	2.1	
		TO-3P	0.7	

FIG.1 Maximum power dissipation versus RMS on-state current

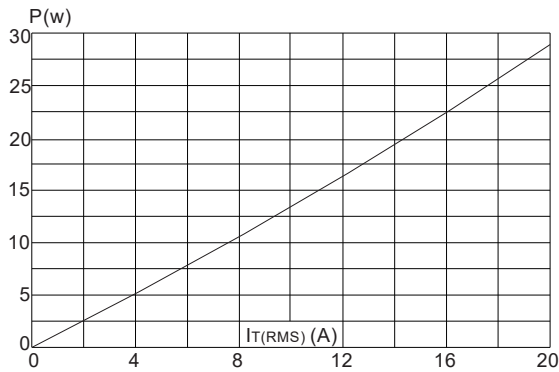


FIG.3: Surge peak on-state current versus number of cycles

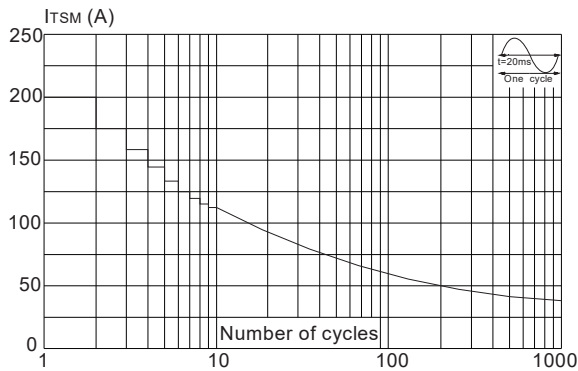


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 100A/\mu s$)

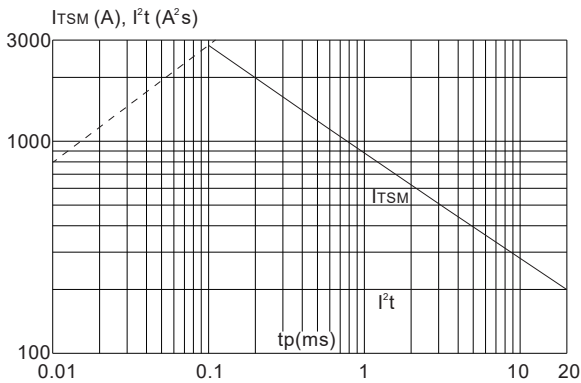


FIG.2: RMS on-state current versus case temperature

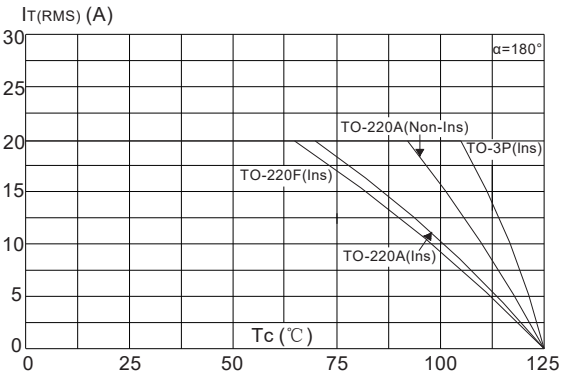


FIG.4: On-state characteristics (maximum values)

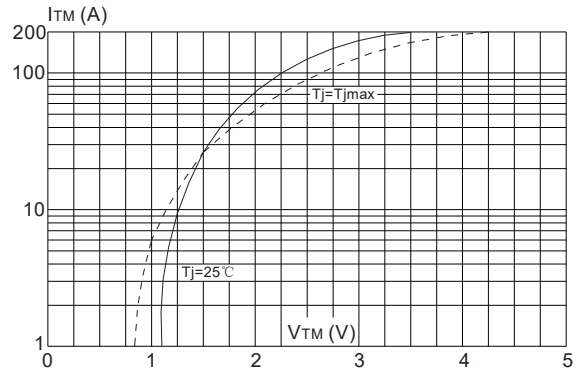


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

